Epitaxial growth of Bi$_2$S$_3$ nanowires on BiVO$_4$ nanostructures for enhancing photoelectrochemical performance

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Supporting Information

Fig. S1 EDX of the Bi$_2$S$_3$/BiVO$_4$ heterojunction films
Fig. S2 XRD pattern of BiVO$_4$ film after LSV measurement in the aqueous solution containing 0.35 M Na$_2$SO$_3$ and 0.25 M Na$_2$S.

Fig. S3 (a) Photocurrent-time plot of the photoelectrodes at 0.6761 V vs. RHE (-0.2 V vs. Ag/AgCl)